

## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.050 at $V_{GS} = 10$ V	3.4
	0.085 at $V_{GS} = 4.5$ V	2.6

### FEATURES

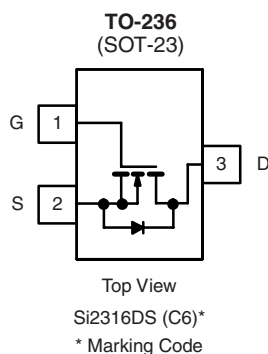
- Halogen-free Option Available
- TrenchFET® Power MOSFET

### APPLICATIONS

- Battery Switch



Available  
**RoHS\***  
COMPLIANT



Ordering Information: Si2316DS-T1  
Si2316DS-T1-E3 (Lead (Pb)-free)  
Si2316DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a, b</sup>	$I_D$	3.4	2.9	A
		2.7	2.3	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	16		
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	$I_S$	0.8		
Power Dissipation <sup>a, b</sup>	$P_D$	0.96	0.7	W
		0.6	0.45	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	100	130	°C/W
		140	175	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	60	75	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

**SPECIFICATIONS**  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

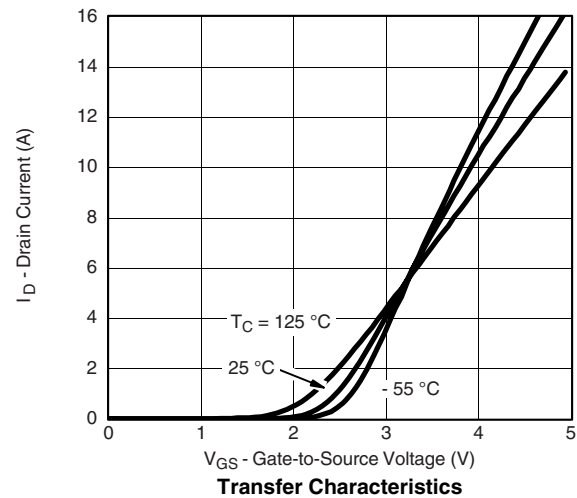
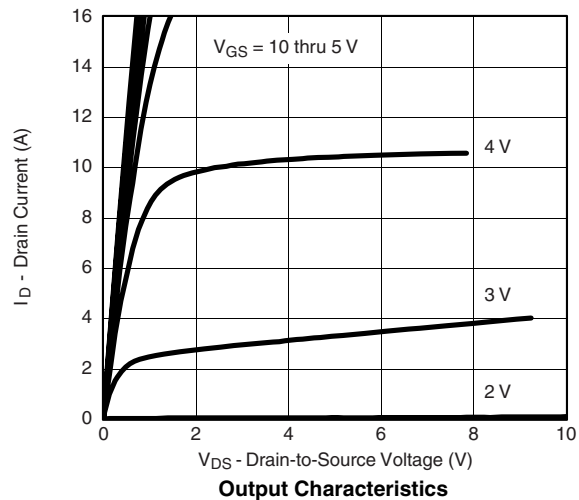
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	0.8			
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$			0.5	$\mu\text{A}$
		$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 4.5\text{ V}$ , $V_{GS} = 10\text{ V}$	6			A
		$V_{DS} \geq 4.5\text{ V}$ , $V_{GS} = 4.5\text{ V}$	4			
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 3.4\text{ A}$		0.042	0.050	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 2.6\text{ A}$		0.068	0.085	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 4.5\text{ V}$ , $I_D = 3.4\text{ A}$		6.0		S
Diode Forward Voltage	$V_{SD}$	$I_S = 0.8\text{ A}$ , $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 3.4\text{ A}$		4.3	7	nC
Gate-Source Charge	$Q_{gs}$			0.65		
Gate-Drain Charge	$Q_{gd}$			1.2		
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		215		pF
Output Capacitance	$C_{oss}$			90		
Reverse Transfer Capacitance	$C_{rss}$			55		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 15\text{ }\Omega$ $I_D \cong 1.0\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_G = 6\text{ }\Omega$		9	15	ns
Rise Time	$t_r$			9	15	
Turn-Off Delay Time	$t_{d(off)}$			14	20	
Fall Time	$t_f$			6	12	

Notes:

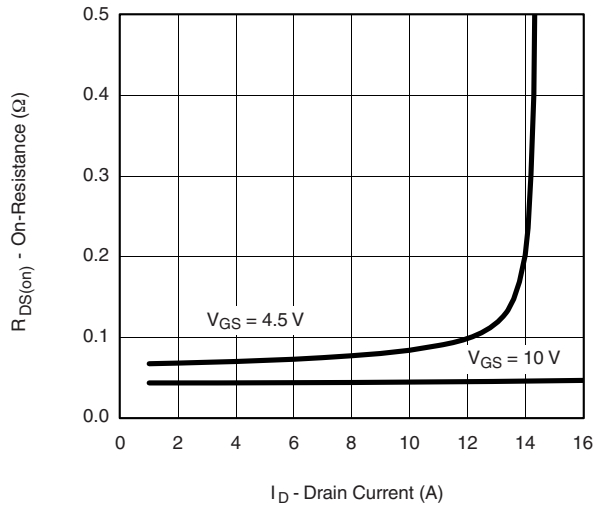
a. Pulse test;  $PW \leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

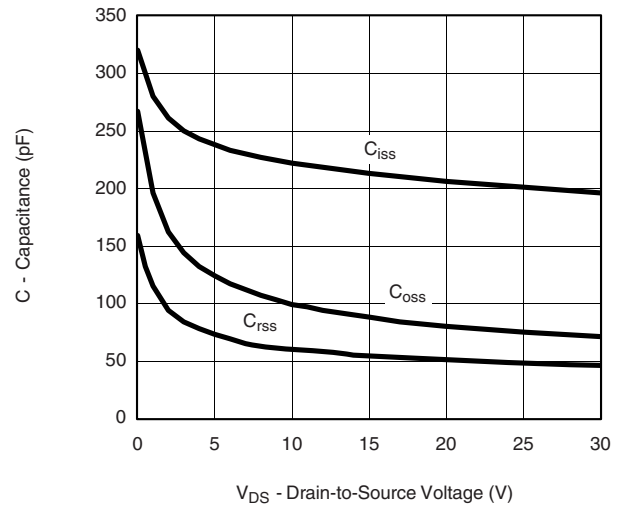
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^{\circ}\text{C}$ , unless otherwise noted

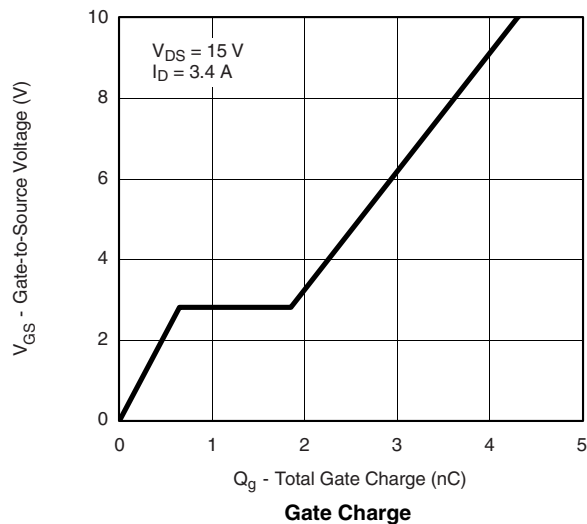
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



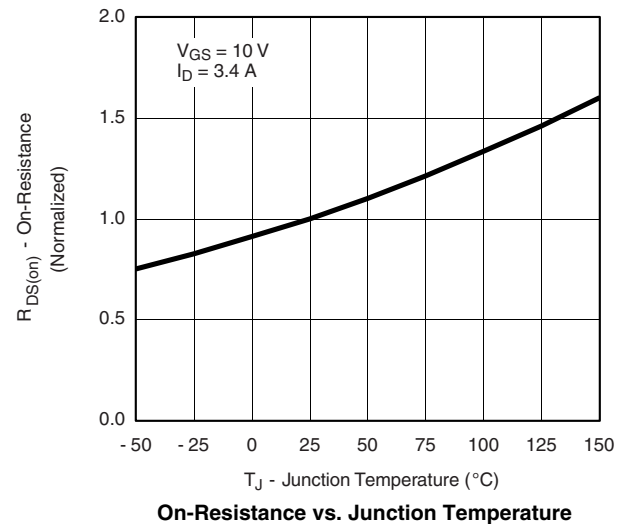
On-Resistance vs. Drain Current



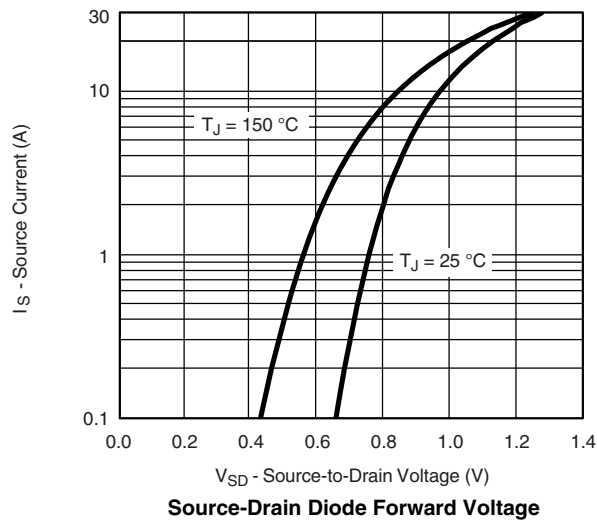
Capacitance



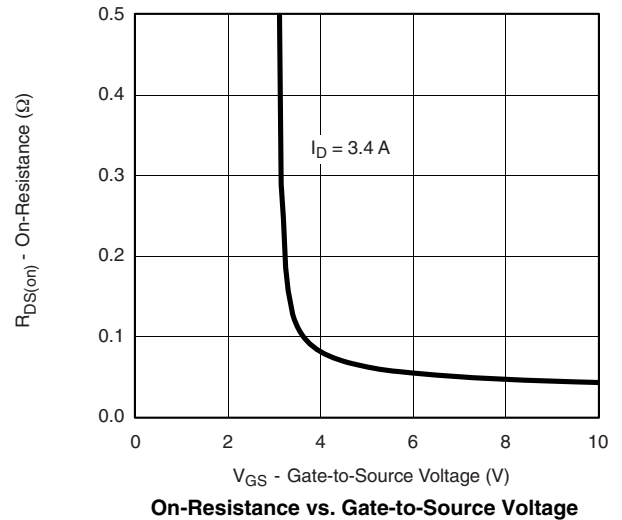
Gate Charge



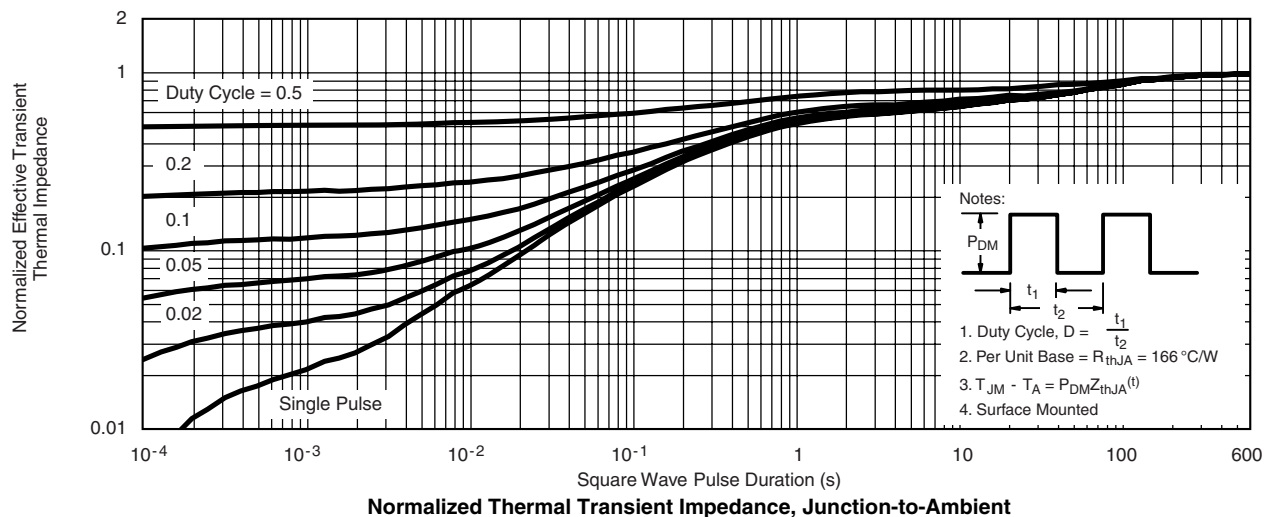
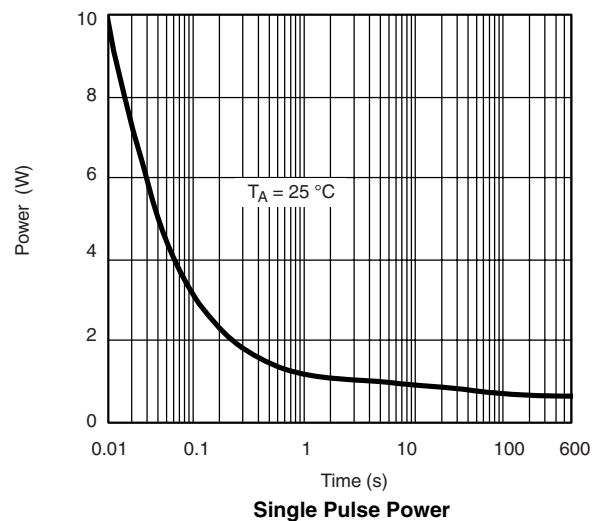
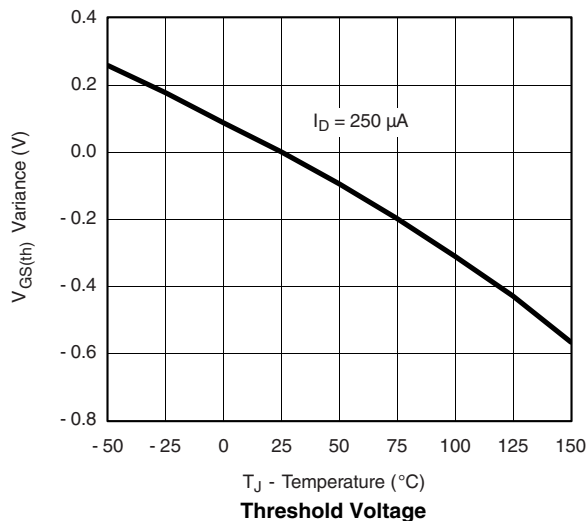
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

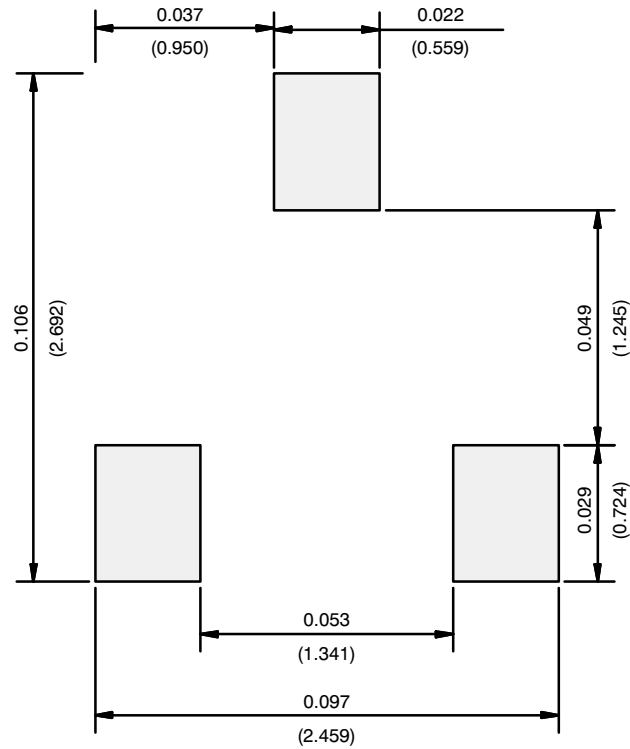
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## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01				
DWG: 5479				

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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